

## Chip Specification

### General Description:

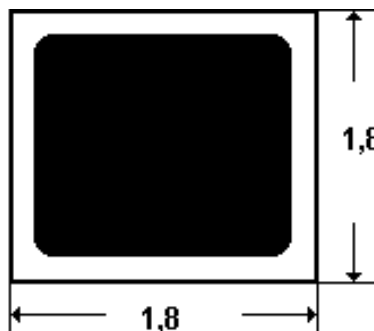
Schottky Diode chips with Mo-barrier for switch mode power rectifiers with the following features:

- \* **Guard-ring for stress protection**
- \* **Extremely low forward voltage**
- \* **125 °C operation junction temperature**
- \* **reverse avalanche behavior**

### Mechanical Data:

#### SB 3XX passivated Silicon Chip

Demension(mm)	1,8x1,8
Thickness:	350 +- 20 $\mu$ m
Metallization:	
Top ( Anode ) :	Al Ag
Bottom ( Cathode ) :	TiNiAg



Forward Current(A)	3 A
Reverse Voltage (V):	23, 43, 100 V

Type	Chip	$V_R(V)$	$V_F(V)@25\text{ C}$	$I_{RM}@V_{RMM}$
	size(mm)		at $I_f=1A$	at 25 C
SB320	1,8x1,8	23 V	440mV	0,5mA
SB340	1,8x1,8	43 V	600mV	0,5mA
SB3100	1,8x1,8	100 V	690mV	0,5mA

Note: Other voltages,  $V_f$  & Top Metal AL are available

